

ABSTRACT OF THE DISCLOSURE

A method is provided for processing a semiconductor topography. In an embodiment, the method includes polishing the topography on a primary polishing pad 5 during a primary polishing step without depositing water on the primary polishing pad. The method may also include transferring the topography from the primary polishing pad to a final polishing pad. A substantial amount of residual slurry particles may be present on the topography while the topography is being transferred. In an embodiment, the method may also include polishing the topography on a final polishing pad during a final 10 polishing step. The final polishing step may include depositing water on the final polishing pad in a plurality of dispense intervals to reduce a rate of change of a pH of a polishing solution on the topography.

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